U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
KM1-001SERIAL NO.
09/652,550LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT: Keiji Jono et al.

FILING DATE
August 31, 2000GROUP
2811

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
qV	AA	6,034,409	03/07/2000	Sakai et al.			
qV	AB	6,171,924 B1	01/09/2001	Wang et al.			
qV	AC	6,154,417	11/28/2000	Kim			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		
	AS		
	AT		

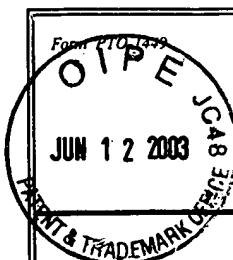
EXAMINER

[Signature]

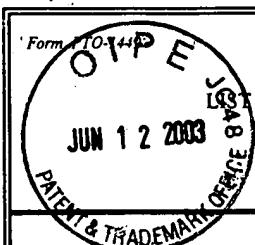
DATE CONSIDERED

08/14/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. KMI-001		SERIAL NO.			
		APPLICANT Keiji Jono et al.					
		FILING DATE		GROUP			
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS						Translation Yes No	
		Document Number	Date	Country	Class		
	AL						
	AM						
	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						TECHNOLOGY CENTER JUN 18 2003	
9V	AR		Shallow Trench Isolation Characteristics with High-Density-Plasma Chemical Vapor Deposition Gap-Fill Oxide for Deep-Submicron CMOS Technologies, Seung-Ho Lee et al., Jpn. J. Appl. Phys. Vol. 37 (1998), pp. 1222-1227.				
9V	AS		Impact of Shallow Trench Isolation on Reliability of Buried- and Surface-Chanel sub- μ m PFET, William Tonni et al., 1995 IEEE, pp. 24-29.				
9V	AT		Subbreakdown Drain Leakage Current in MOSFET, J. Chen et al., 1987 IEEE, pp.515-517.				
EXAMINER <i>[Signature]</i>			DATE CONSIDERED 08/14/03				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

RECEIVED



U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.
KMI-001

SERIAL NO.

APPLICANT
Keiji Jono et al.

FILING DATE

GROUP

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

TECHNOLOGY CENTER
REC'D IN
JUN 8 2003
2000

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	IT Translation Fee No
	AL						2000
	AM						
	AN						
	AO						
	AP						

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

qV	AR		Shallow Trench Isolation for advanced ULSI CMOS Technologies, M. Nandakumar et al, Silicon Technology Development, Kilby Center, Texas Instruments, Undated, 4 pages.				
	AS						
	AT						

EXAMINER

Janice

DATE CONSIDERED

08/14/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.